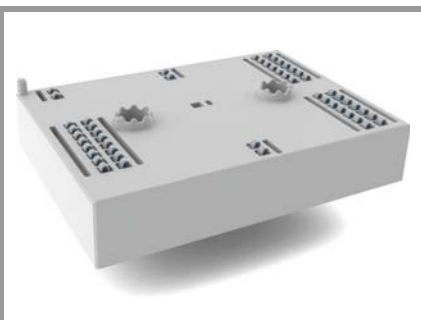


# SKiiP 38GB07E3V1



MiniSKiiP® 3 Dual

## Half-Bridge

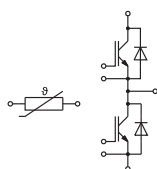
### SKiiP 38GB07E3V1

#### Features\*

- 650V Trench IGBTs
- Robust and soft diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532
- NTC T-Sensor

#### Remarks

- Max. case temperature limited to  $T_C = 125^\circ\text{C}$
- Product reliability results valid for  $T_j \leq 150^\circ\text{C}$  (recommended  $T_{j,op} = -40 \dots +150^\circ\text{C}$ )

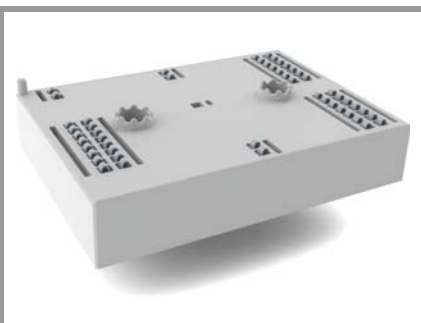


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Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
<b>Inverter - IGBT</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$		650	V
$I_C$	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	287	A
		$T_s = 70^\circ\text{C}$	228	A
$I_{Cnom}$			300	A
$I_{CRM}$			900	A
$V_{GES}$			-20 ... 20	V
$t_{psc}$	$V_{CC} = 360\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 650\text{ V}$	$T_j = 150^\circ\text{C}$	6	$\mu\text{s}$
$T_j$			-40 ... 175	$^\circ\text{C}$
<b>Inverse - Diode</b>				
$I_F$	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	310	A
		$T_s = 70^\circ\text{C}$	241	A
$I_{FRM}$			600	A
$I_{FSM}$	10 ms, sin 180°, $T_j = 150^\circ\text{C}$		1980	A
$T_j$			-40 ... 175	$^\circ\text{C}$
<b>Module</b>				
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}$ , $T_{terminal} = 80^\circ\text{C}$ , 20A per spring		280	A
$T_{stg}$	module without TIM		-40 ... 125	$^\circ\text{C}$
$V_{isol}$	AC sinus 50 Hz, $t = 1\text{ min}$		2500	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
<b>Inverter - IGBT</b>						
$V_{CE(sat)}$	$I_C = 300\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.45	1.90		V
		$T_j = 150^\circ\text{C}$	1.70	2.10		V
$V_{CE0}$	chipelevel	$T_j = 25^\circ\text{C}$	0.90	1.00		V
		$T_j = 150^\circ\text{C}$	0.82	0.90		V
$r_{CE}$	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.83	3.0		m $\Omega$
		$T_j = 150^\circ\text{C}$	2.9	4.0		m $\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}$ , $I_C = 4.8\text{ mA}$		5.1	5.8	6.4	V
$I_{CES}$	$V_{GE} = 0\text{ V}$ $V_{CE} = 650\text{ V}$	$T_j = 25^\circ\text{C}$			3.0	mA
					-	mA
$C_{ies}$	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	18.48			nF
$C_{oes}$		$f = 1\text{ MHz}$	1.16			nF
$C_{res}$		$f = 1\text{ MHz}$	0.55			nF
$Q_G$	- 8 V...+ 15 V		2400			nC
$R_{Gint}$	$T_j = 25^\circ\text{C}$		1.0			$\Omega$
$t_{d(on)}$	$V_{CC} = 300\text{ V}$	$T_j = 150^\circ\text{C}$	86			ns
$t_r$	$I_C = 300\text{ A}$	$T_j = 150^\circ\text{C}$	73			ns
$E_{on}$	$R_{Gon} = 3\ \Omega$	$T_j = 150^\circ\text{C}$	5.5			mJ
$t_{d(off)}$	$R_{Goff} = 3\ \Omega$	$T_j = 150^\circ\text{C}$	530			ns
		$T_j = 150^\circ\text{C}$	64			ns
$t_f$	$di/dt_{off} = 5375\text{ A}/\mu\text{s}$ $dv/dt = 4000\text{ V}/\mu\text{s}$	$T_j = 150^\circ\text{C}$				ns
$E_{off}$	$V_{GE} = +15/-8\text{ V}$ $L_s = 25\text{ nH}$	$T_j = 150^\circ\text{C}$		10.6		mJ
$R_{th(j-s)}$	per IGBT, $\lambda_{paste} = 0.8\text{ W}/(\text{K}^*\text{m})$		0.25			K/W

# SKiiP 38GB07E3V1



MiniSKiiP® 3 Dual

## Half-Bridge

### SKiiP 38GB07E3V1

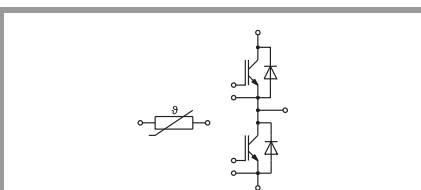
#### Features\*

- 650V Trench IGBTs
- Robust and soft diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532
- NTC T-Sensor

#### Remarks

- Max. case temperature limited to  $T_C = 125^\circ\text{C}$
- Product reliability results valid for  $T_j \leq 150^\circ\text{C}$  (recommended  $T_{j,op} = -40 \dots +150^\circ\text{C}$ )

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
<b>Inverse - Diode</b>						
$V_F = V_{EC}$	$I_F = 300\text{ A}$ $V_{GE} = 0\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$		1.40	1.76	V
		$T_j = 150^\circ\text{C}$		1.39	1.77	V
$V_{F0}$	chipelevel	$T_j = 25^\circ\text{C}$		1.04	1.24	V
		$T_j = 150^\circ\text{C}$		0.85	0.99	V
$r_F$	chipelevel	$T_j = 25^\circ\text{C}$		1.19	1.76	m $\Omega$
		$T_j = 150^\circ\text{C}$		1.79	2.6	m $\Omega$
$I_{RRM}$	$I_F = 300\text{ A}$	$T_j = 150^\circ\text{C}$		247		A
$Q_{rr}$	$di/dt_{off} = 4990\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		22.6		$\mu\text{C}$
$E_{rr}$	$V_{GE} = -8\text{ V}$ $V_{CC} = 300\text{ V}$	$T_j = 150^\circ\text{C}$		5.1		mJ
$R_{th(j-s)}$	per Diode, $\lambda_{paste} = 0.8\text{ W}/(\text{K}\cdot\text{m})$			0.28		K/W
<b>Module</b>						
$L_{CE}$				15		nH
$M_s$	to heat sink		2		2.5	Nm
$w$				76		g
<b>Temperature Sensor</b>						
$R_{100}$	$T_c = 100^\circ\text{C}$ ( $R_{25} = 5\text{ k}\Omega$ )			$493 \pm 5\%$		$\Omega$
$B_{25/85}$	$R(T) = R_{25} \cdot \exp[B_{25/85} \cdot (1/T - 1/298)]$ , $T[\text{K}]$			3420		K



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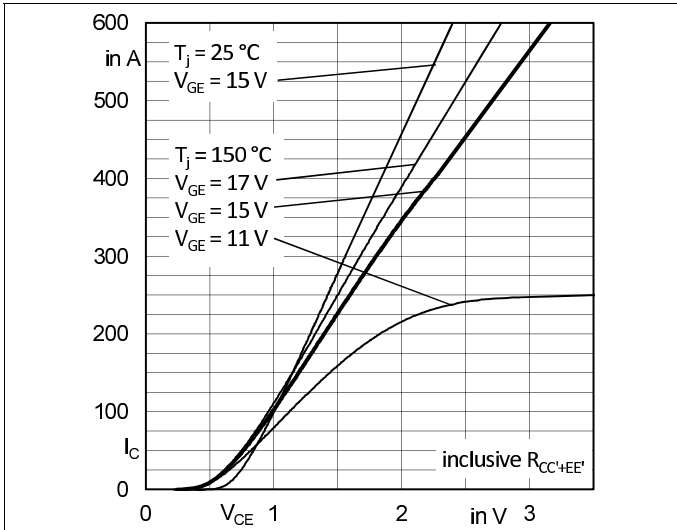


Fig. 1: Typ. output characteristic

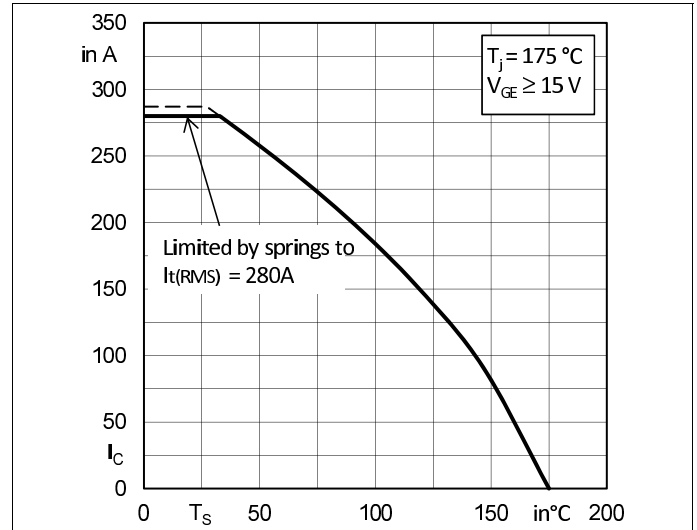


Fig. 2: Rated current vs. temperature  $I_C = f(T_s)$

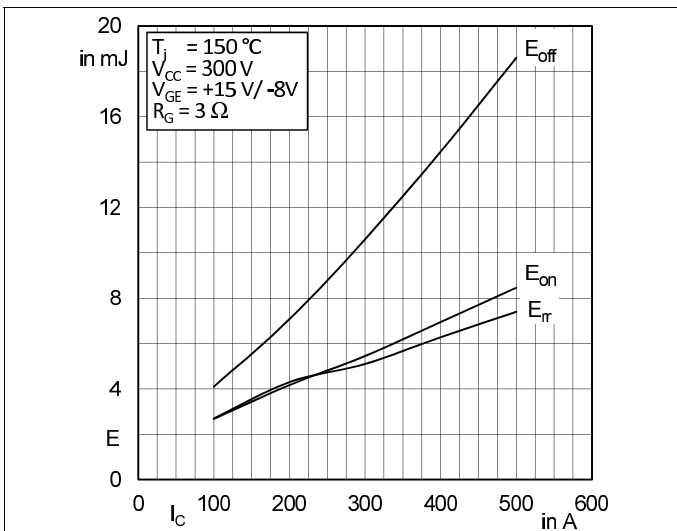


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$

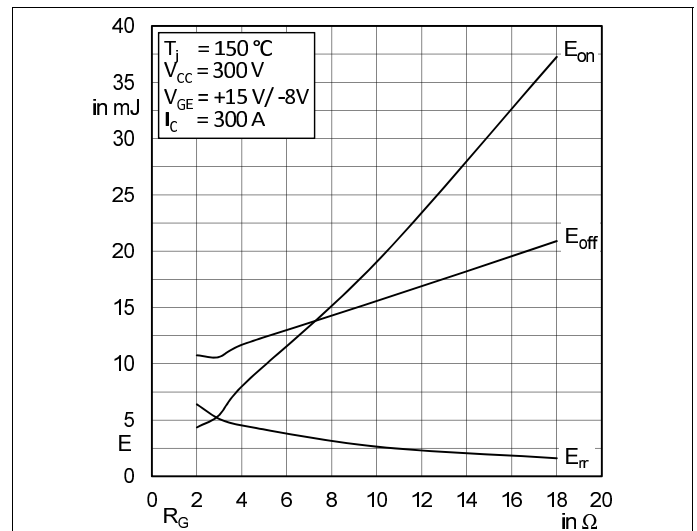


Fig. 4: Typ. turn-on /-off energy =  $f(R_G)$

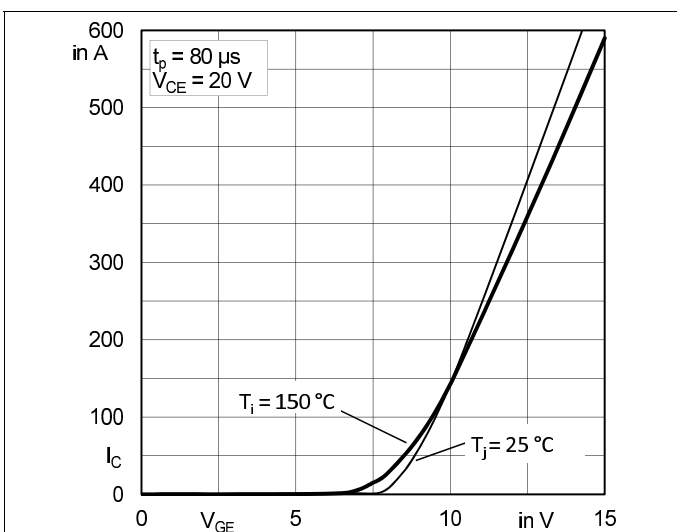


Fig. 5: Typ. transfer characteristic

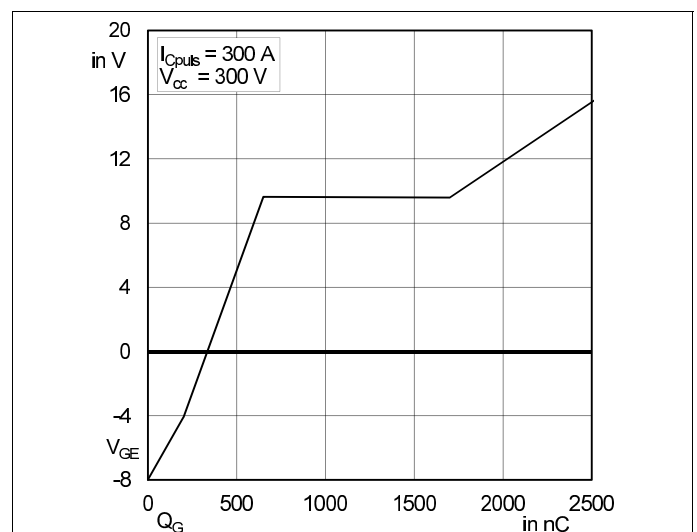


Fig. 6: Typ. gate charge characteristic

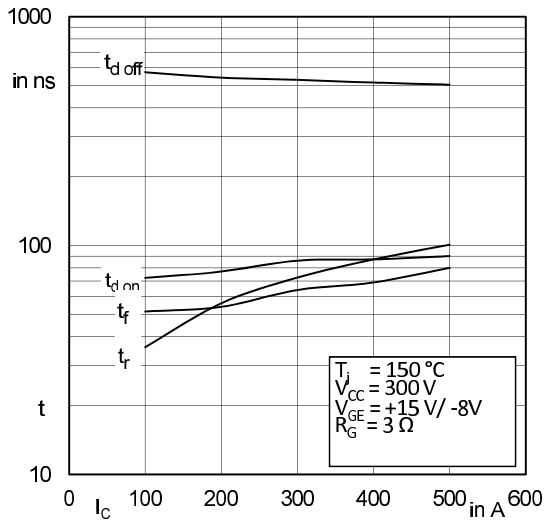


Fig. 7: Typ. switching times vs.  $I_c$

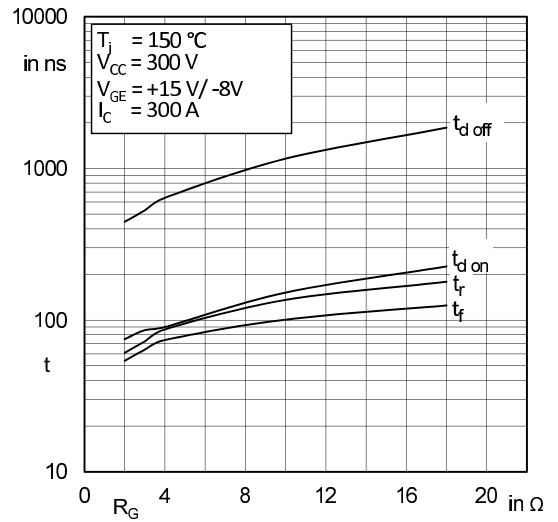


Fig. 8: Typ. switching times vs. gate resistor  $R_G$

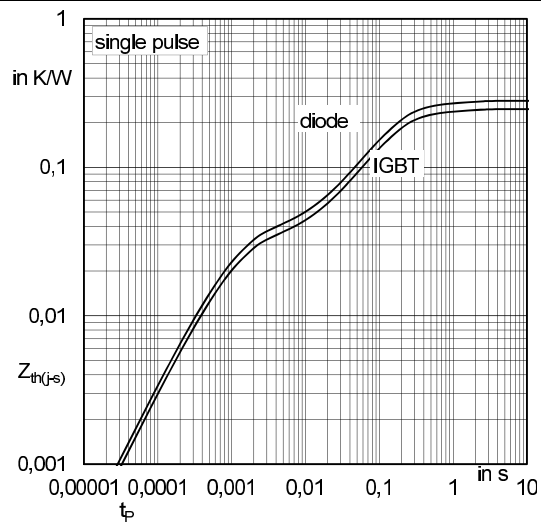


Fig. 9: Typ. transient thermal impedance

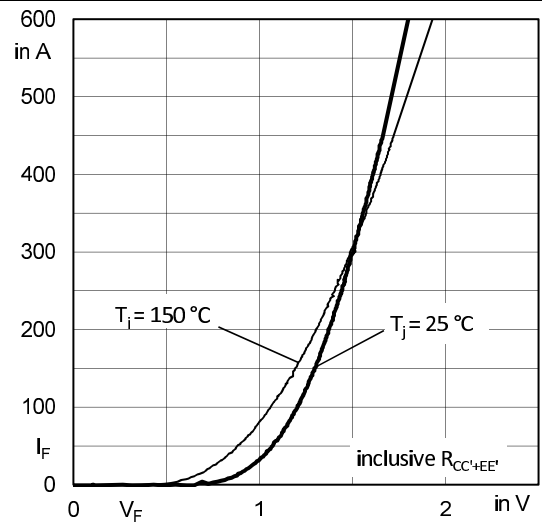


Fig. 10: Typ. CAL diode forward characteristic

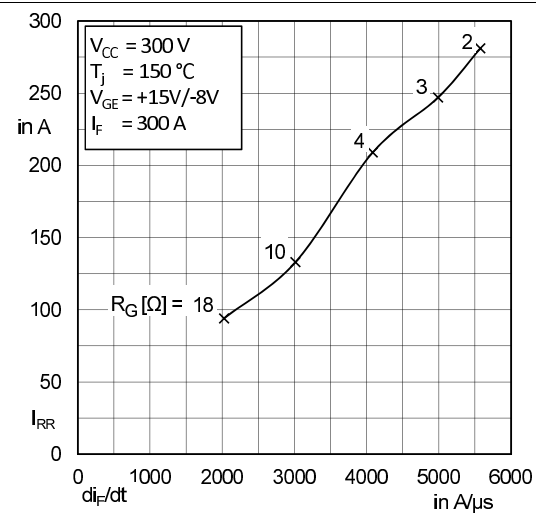


Fig. 11: Typ. CAL diode peak reverse recovery current

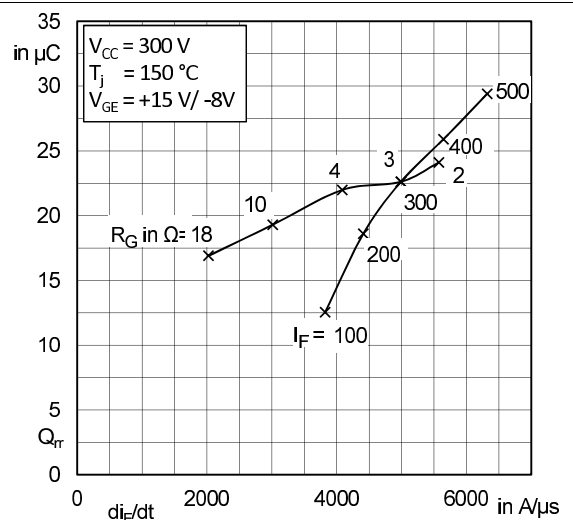
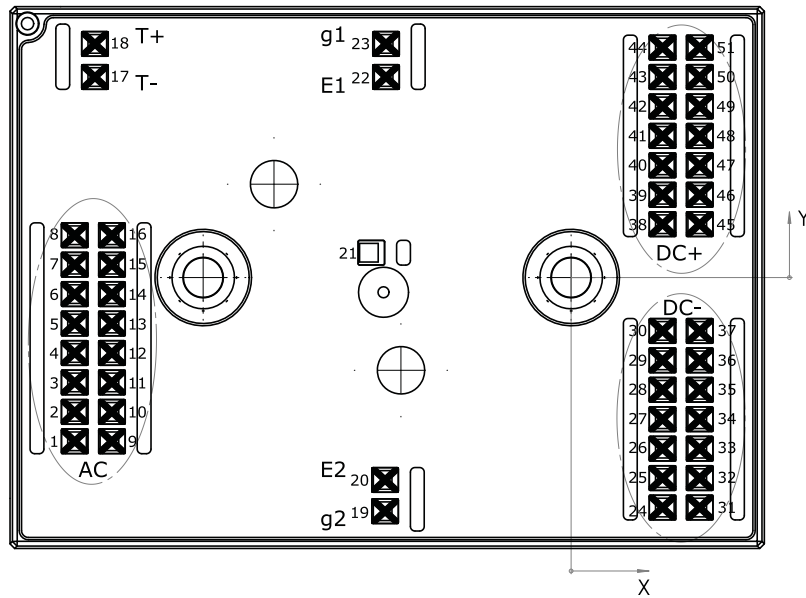


Fig. 12: Typ. CAL diode recovery charge

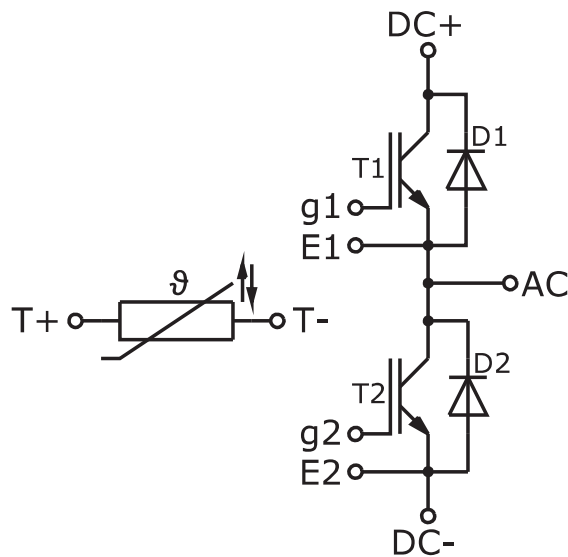
# SKiiP 38GB07E3V1

Pin out											
Pin	X	Y	Function	Pin	X	Y	Function	Pin	X	Y	Function
1	-53,98	-17,80	AC	18	-51,78	25,40	T+	35	13,98	-12,20	DC-
2	-53,98	-14,60	AC	19	-20,23	-25,40	g2	36	13,98	-9,00	DC-
3	-53,98	-11,40	AC	20	-20,23	-22,00	E2	37	13,98	-5,80	DC-
4	-53,98	-8,20	AC	21	-21,73	2,70		38	9,93	5,80	DC+
5	-53,98	-5,00	AC	22	-20,13	21,80	E1	39	9,93	9,00	DC+
6	-53,98	-1,80	AC	23	-20,13	25,40	g1	40	9,93	12,20	DC+
7	-53,98	1,40	AC	24	9,93	-25,00	DC-	41	9,93	15,40	DC+
8	-53,98	4,60	AC	25	9,93	-21,80	DC-	42	9,93	18,60	DC+
9	-49,93	-17,80	AC	26	9,93	-18,60	DC-	43	9,93	21,80	DC+
10	-49,93	-14,60	AC	27	9,93	-15,40	DC-	44	9,93	25,00	DC+
11	-49,93	-11,40	AC	28	9,93	-12,20	DC-	45	13,98	5,80	DC+
12	-49,93	-8,20	AC	29	9,93	-9,00	DC-	46	13,98	9,00	DC+
13	-49,93	-5,00	AC	30	9,93	-5,80	DC-	47	13,98	12,20	DC+
14	-49,93	-1,80	AC	31	13,98	-25,00	DC-	48	13,98	15,40	DC+
15	-49,93	1,40	AC	32	13,98	-21,80	DC-	49	13,98	18,60	DC+
16	-49,93	4,60	AC	33	13,98	-18,60	DC-	50	13,98	21,80	DC+
17	-51,78	21,80	T-	34	13,98	-15,40	DC-	51	13,98	25,00	DC+

all values in [mm]



Pinout and Dimensions



Pinout

This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

## **\*IMPORTANT INFORMATION AND WARNINGS**

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